

## Amended Claims

1. (withdrawn) A LVTSCR-like structure having one or more diodes formed in a p-well of the structure.
2. (currently amended) A method of increasing the holding voltage of a LVTSCR structure that includes an n-well and a p-well formed in a substrate, an n+ region and a p+ region formed in the n-well, and ~~a~~ an n+ region and a p+ region formed in the p-well, the method comprising forming at least one additional p+ region and at least one additional n+ region inside ~~a~~ the p-well of the structure to define at least one p-n junction between one of the ~~at least one~~ p+ regions and the at least one of the ~~additional~~ n+ regions in the p-well that is forward biased during normal operation.
3. (currently amended) A method of increasing the holding voltage of a LVTSCR structure having an anode in an n-well and a cathode in a p-well, the cathode being defined by an n+ region and a p+ region, comprising forming at least one additional n+ region and at least one additional p+ region in the p-well to define at least one forward biased diode in the p-well, thereby providing an alternative current path from anode to cathode through said at least one diode ~~highly doped n+ region and at least one highly doped p+ region formed in the p-well of the structure, the at least one highly doped n+ region and at least one highly doped p+ region formed in the p-well being forward biased relative to each other during normal operation.~~
4. (original) A method of claim 3, wherein the alternative current path defines a lower resistance current path than the p-well.
5. (canceled)
6. (canceled)
7. (canceled)
8. (canceled)